

## TSM190N08

### 75V N-Channel Power MOSFET

## Pb RoHS

TO-220



#### Pin Definition:

- 1. Gate
- 2. Drain
- 3. Source

#### **PRODUCT SUMMARY**

V <sub>DS</sub> (V)	$R_{DS(on)}(m\Omega)$	I <sub>D</sub> (A)
75	4.2 @ V <sub>GS</sub> =10V	190

#### **Features**

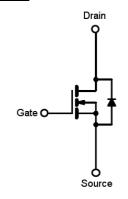
- Advanced Trench Technology
- Low R<sub>DS(ON)</sub> 4.2mΩ (Max.)
- Low gate charge typical @ 160nC (Typ.)
- Low Crss typical @ 300pF (Typ.)

#### **Ordering Information**

Part No.	Package	Packing
TSM190N08CZ C0G	TO-220	50pcs / Tube

Note: "G" denote for Halogen Free Product.

#### **Block Diagram**



N-Channel MOSFET

#### **Absolute Maximum Rating** (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V <sub>DS</sub>	75	V	
Gate-Source Voltage		$V_{GS}$	±20	V	
	T <sub>C</sub> =25°C		190		
Continuous Drain Current $T_{C}=70^{\circ}C$ $T_{C}=70^{\circ}C$ $T_{C}=70^{\circ}C$		150	۸		
Continuous Drain Current	T <sub>A</sub> =25°C	I <sub>D</sub>	17	А	
	T <sub>A</sub> =70°C	1	14		
Drain Current-Pulsed Note 1		I <sub>DM</sub>	600	Α	
Avalanche Current, L=0.3mH		I <sub>AS</sub> , I <sub>AR</sub>	113	Α	
Avalanche Energy, L=0.3mH		E <sub>AS</sub> , E <sub>AR</sub>	1900	mJ	
	T <sub>C</sub> =25°C		250		
Maximum Dawar Dissipation	T <sub>C</sub> =70°C		160	W	
Maximum Power Dissipation	T <sub>A</sub> =25°C	− P <sub>D</sub>	2		
	T <sub>A</sub> =70°C		1.3		
Storage Temperature Range		T <sub>STG</sub>	-55 to +150	°C	
Operating Junction Temperature Range		T <sub>J</sub>	-55 to +150	°C	

<sup>\*</sup> Limited by maximum junction temperature

#### **Thermal Performance**

Parameter	Symbol	Limit	Unit
Thermal Resistance - Junction to Case	R⊖ <sub>JC</sub>	0.5	°C/W
Thermal Resistance - Junction to Ambient	$R\Theta_{JA}$	62.5	°C/W

Notes: Surface mounted on FR4 board t ≤ 10sec



### **TSM190N08**

Version: B15

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**Electrical Specifications** (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250uA$	BV <sub>DSS</sub>	75			V
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 90A$	R <sub>DS(ON)</sub>	1	3.4	4.2	mΩ
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250uA$	$V_{GS(TH)}$	2	3	4	V
Zero Gate Voltage Drain Current	$V_{DS} = 75V, V_{GS} = 0V$	I <sub>DSS</sub>	1		1	uA
Gate Body Leakage	$V_{GS} = \pm 25V, V_{DS} = 0V$	I <sub>GSS</sub>	1		±100	nA
Dynamic						
Total Gate Charge	V 20V I 20A	$Q_g$	1	160		
Gate-Source Charge	$V_{DS} = 30V, I_D = 90A,$ $V_{GS} = 10V$	$Q_{gs}$		35		nC
Gate-Drain Charge		$Q_{gd}$		40		
Input Capacitance	$V_{DS} = 30V, V_{GS} = 0V,$	C <sub>iss</sub>		8600		
Output Capacitance		C <sub>oss</sub>	1	780		pF
Reverse Transfer Capacitance	f = 1.0MHz	C <sub>rss</sub>	1	300		
Switching						
Turn-On Delay Time		t <sub>d(on)</sub>		25		
Turn-On Rise Time	$V_{GS} = 10V, V_{DS} = 30V,$	t <sub>r</sub>		40		~ C
Turn-Off Delay Time	$R_G = 3.3\Omega$	$t_{d(off)}$		85		nS
Turn-Off Fall Time		t <sub>f</sub>		45		
Drain-Source Diode Characteristics and Maximum Rating						
Drain-Source Diode Forward Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =90A	V <sub>SD</sub>	-	0.8	1.3	V
Reverse Recovery Time	I <sub>S</sub> = 90A, T <sub>J</sub> =25 °C	t <sub>fr</sub>		70		nS
Reverse Recovery Charge	dl/dt = 100A/us	Q <sub>fr</sub>		115		nC

Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
 R<sub>ΘJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R<sub>ΘJC</sub> is guaranteed by design while R<sub>ΘCA</sub> is determined by the user's board design. R<sub>ΘJA</sub> shown below for single device operation on FR-4 in still air

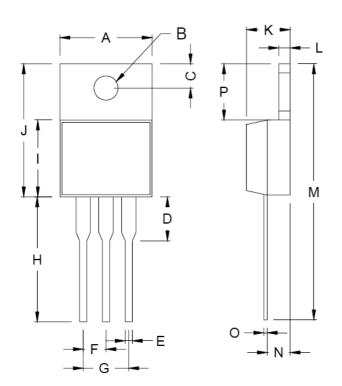


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### **TO-220 Mechanical Drawing**



TO-220 DIMENSION						
DIM	MILLIM	MILLIMETERS		INCHES		
DIIVI	MIN	MAX	MIN	MAX		
Α	10.000	10.500	0.394	0.413		
В	3.740	3.910	0.147	0.154		
С	2.440	2.940	0.096	0.116		
D	•	6.350	-	0.250		
Е	0.381	1.106	0.015	0.040		
F	2.345	2.715	0.092	0.058		
G	4.690	5.430	0.092	0.107		
Н	12.700	14.732	0.500	0.581		
J	14.224	16.510	0.560	0.650		
K	3.556	4.826	0.140	0.190		
L	0.508	1.397	0.020	0.055		
М	27.700	29.620	1.060	1.230		
Ν	2.032	2.921	0.080	0.115		
0	0.255	0.610	0.010	0.024		
Р	5.842	6.858	0.230	0.270		



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